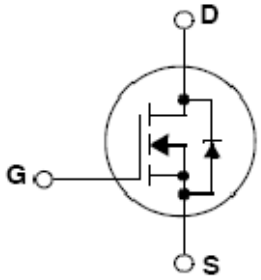
BYD Microelectronics Co., Ltd.

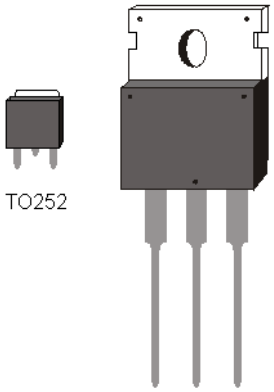
BF95N50T/BF95N50L

500V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using VDMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.





Features

- V_{DS} =500 V
- I_D=5A
- $R_{DS(ON)}$≤1.60Ω TYP(V_{GS}=10V,I_D=2.5A)
- Low C_{RSS} (typical 7.8 pF)
- Fast switching

Absolute Maximum Ratings

Symbol	Parameter	BF95N50T	BF95N50L	Unit
V_{DS}	Drain-Source Voltage	500		V
I_D	Drain Current(continuous)at Tc=25°C	5		A
I_{DM}	Drain Current (pulsed) (Note1)	20		A
V_{GS}	Gate-Source Voltage	±30		V
I_{AR}	Avalanche Current (Note1)	5		A
E_{AS}	Single Pulse Avalanche Energy (Note2)	220		mJ
E_{AR}	Repetitive Avalanche Energy (Note1)	6.9		mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	5.0		V/ns
P_D	Power Dissipation (T_C = 25°C)	69		W
Tstg	Storage Temperature Range	-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering Purpose	300		°C

Ordering Information

Part Number	Package	Packaging
BF95N50T	TO-252	Tape&Reel
BF95N50L	TO-220	Tube

Thermal Data

Symbol	Parameter	BF95N50T	BF95/N50L	Unit
Rthj-case	Thermal Resistance Junction- case	1.8		°C /W
Rthj-amb	Thermal Resistance Junction-ambient	62.5		°C /W

Electrical Characteristics(T_c = 25℃)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D=250uA ,V_{GS}=0V	500			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=500V ,V_{GS}=0V			10	uA
		V_{DS}=500V,V_{GS}=0V,Tc=125℃			100	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±30V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2.0		4.0	V
$R_{DS(on)}$	Static Drain-Source On Resistance	V_{GS}=10V,I_D =2.5A			1.6	Ω
C_{iss}	Input Capacitance	V_{DS}=25V,f=1MHZ,V_{GS}=0V		580		pF
C_{oss}	Output Capacitance			75		pF
C_{rss}	Reverse Transfer Capacitance			7.8		pF
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=250V, I_D=2.5A V_{GS}=10V, R_G=4.7Ω (Note4, 5)		26		ns
t_r	Rise Time			20		ns
$t_{d(off)}$	Turn-Off Delay Time			45		ns
t_f	Fall Time			22		ns
Q_g	Total Gate Charge	V_{DD}=400V, I_D=5A V_{GS}=10V (Note4, 5)		20		nC
Q_{gs}	Gate-Source Charge			5		nC
Q_{gd}	Gate-Drain Charge			8		nC
V_{SD}(*)	Forward On Voltage	I_F=5A ,V_{GS}=0V			1.2	V
T_{rr}	Reverse Recovery Time	I_F=5A, di/dt=100A/us (Note4)		350		ns

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 20mH, I_{AS} = 4.5 A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 4.5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J ≤Tjmax
4. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 1.5%
5. Essentially independent of operating temperature
(*)Pulsed:Pulse duration

Typical characteristics (25℃ unless noted)

Figure 1 Output Characteristics

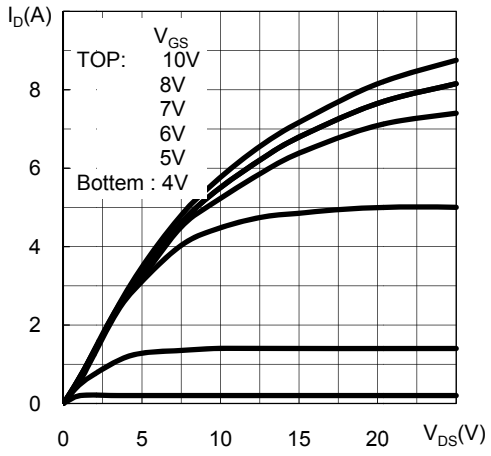


Figure 2 Transfer Characteristics

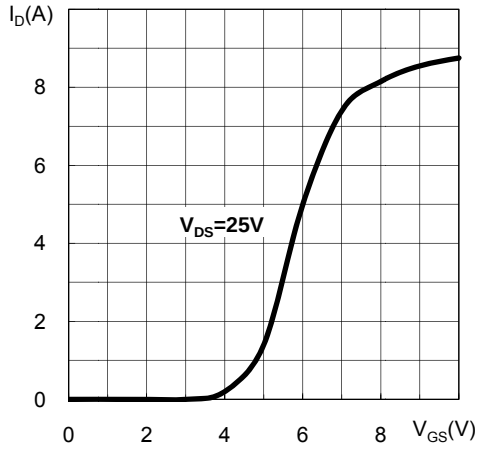


Figure 3 Normalized Threshold Voltage vs. Temperature

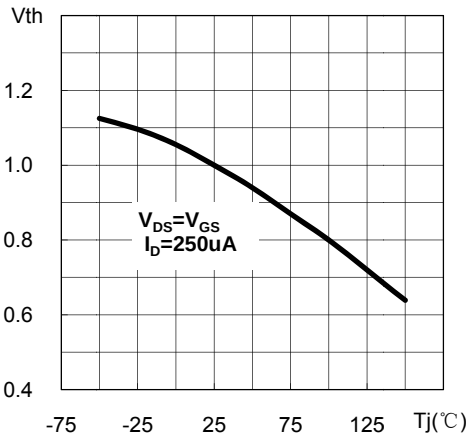


Figure 4 Normalized BV_{DSS} vs.Temperature

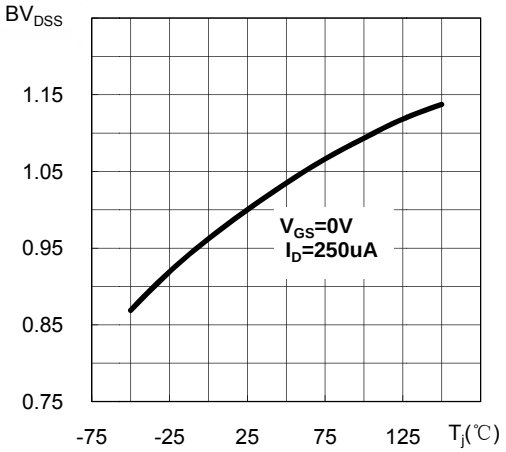


Figure 5 Normalized on Resistance vs Temperature

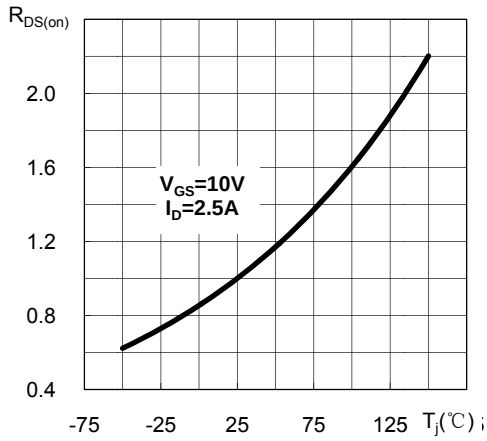


Figure 6 Source-Drain Diode Forward Characteristics

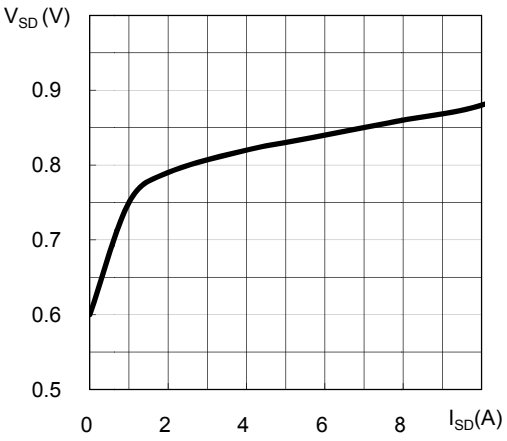


Figure 7 Capacitance

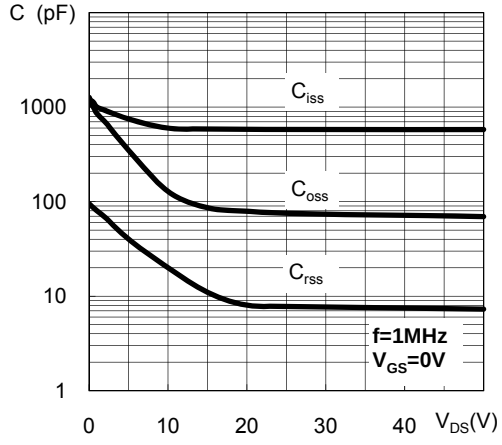


Figure 8 Gate Charge

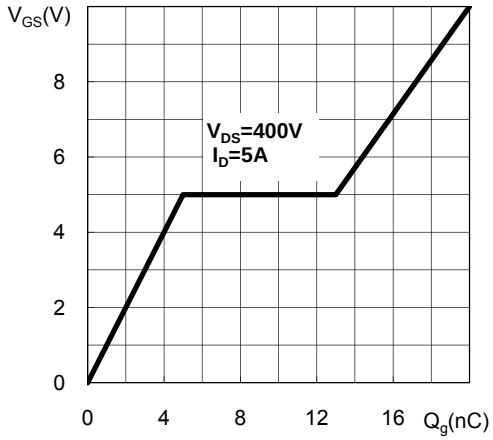


Figure 9 Maximum Safe Operating Area For BF95N50T / BF95N50L

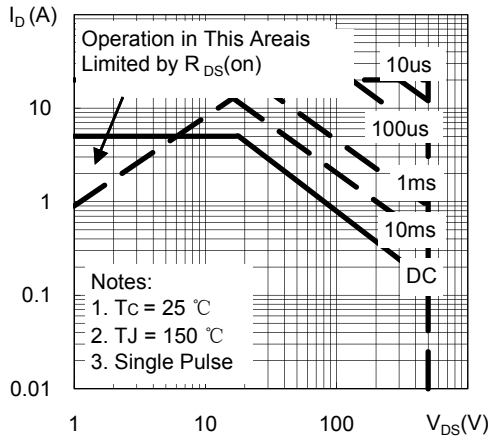


Figure 10 Maximum Drain Current vs Case Temperature

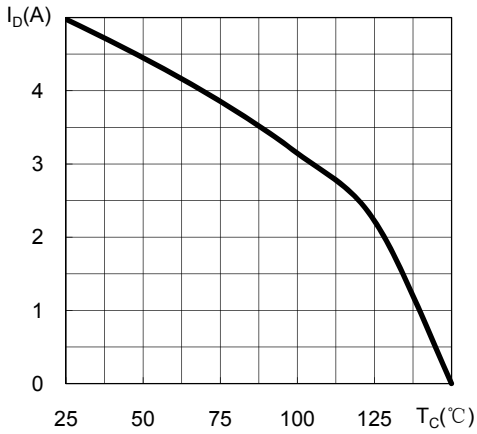
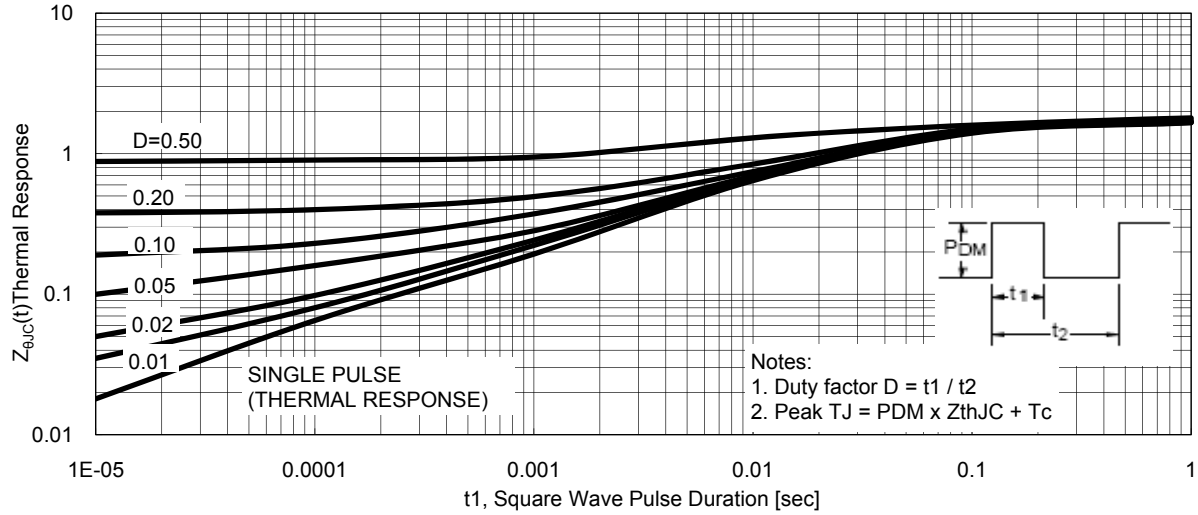
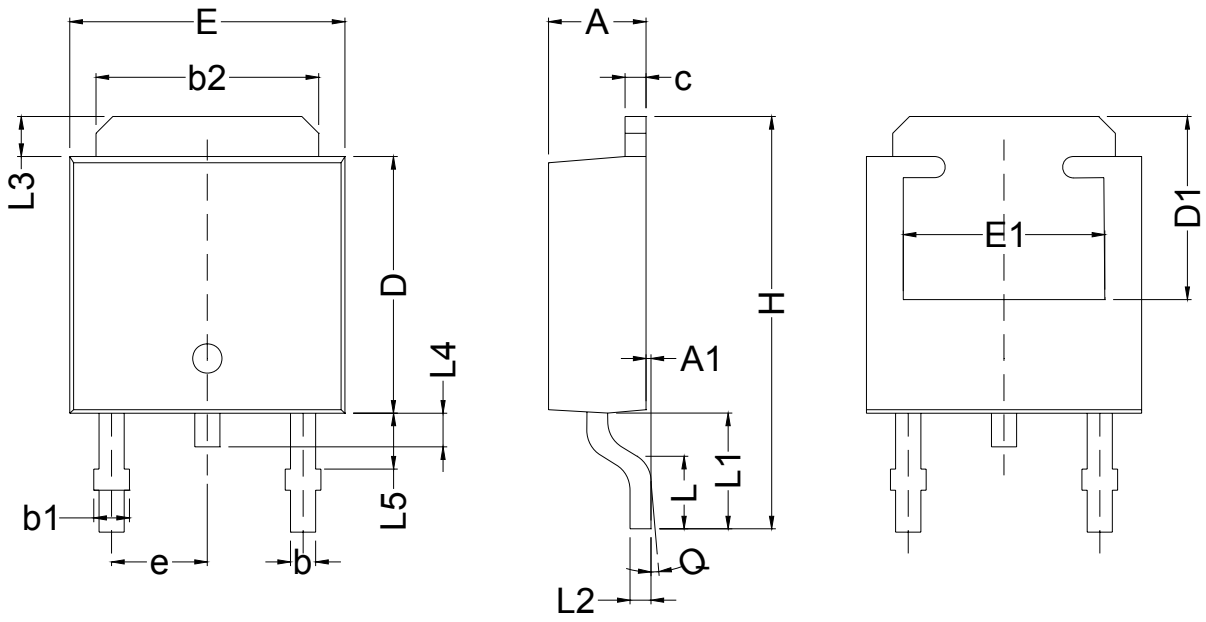


Figure 11 Maximum Transient Thermal Impedance For BF95N50T / BF95N50L

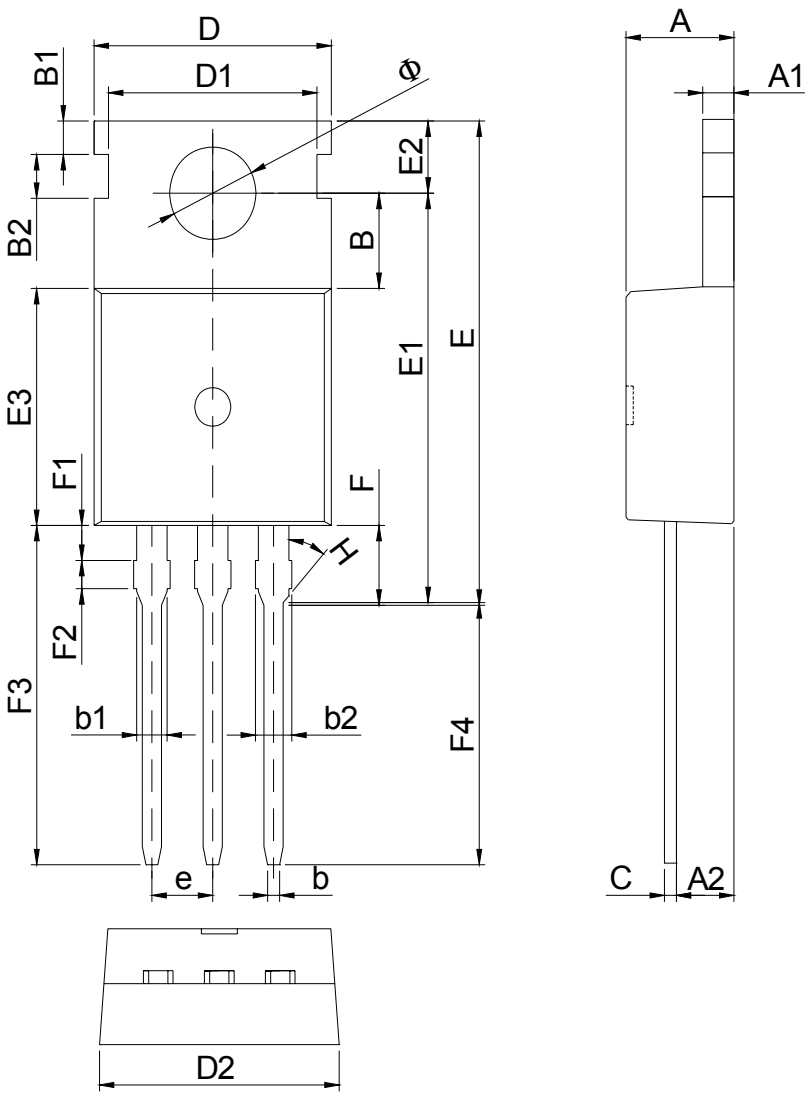


Package Drawing
TO-252



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.22	2.32	2.42	0.087	0.091	0.095
A1	-	-	0.125	-	-	0.005
b	0.55	0.61	0.67	0.022	0.024	0.026
b1	0.76	0.86	0.96	0.030	0.034	0.038
b2	5.20	5.30	5.40	0.205	0.209	0.213
c	0.45	0.50	0.55	0.018	0.020	0.022
D	5.95	6.10	6.25	0.234	0.240	0.246
D1	4.20	4.35	4.50	0.165	0.171	0.177
E	6.40	6.55	6.70	0.252	0.258	0.264
E1	4.75	4.80	4.85	0.187	0.189	0.191
e	2.28REF			0.09REF		
H	9.44	9.79	10.14	0.372	0.385	0.399
L	1.37	1.52	1.67	0.054	0.060	0.066
L1	2.75REF			0.108REF		
L2	0.50REF			0.020REF		
L3	0.90	0.95	1.00	0.035	0.037	0.039
L4	0.65	0.80	0.95	0.026	0.031	0.037
L5	1.14	1.33	1.52	0.045	0.052	0.060
Q	0°	-	6°	0°	-	6°

TO-220



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.45	4.50	4.55	0.175	0.177	0.179
A1	1.25	1.30	1.35	0.049	0.051	0.053
A2	2.20	2.40	2.60	0.087	0.094	0.102
B	-	3.70	-	-	0.146	-
B1	-	1.30	-	-	0.051	-
B2	-	1.70	-	-	0.067	-
b	0.70	0.80	0.90	0.028	0.031	0.035
b1	1.25	1.27	1.29	0.049	0.050	0.051
b2	1.42	1.52	1.62	0.056	0.060	0.064
C	0.45	0.50	0.55	0.018	0.020	0.022
D	9.85	9.90	9.95	0.388	0.390	0.392
D1	-	8.70	-	-	0.343	-
D2	9.98	10.00	10.02	0.393	0.394	0.394
E	-	-	18.95	-	-	0.746
E1	-	15.90	-	-	0.626	-
E2	-	2.80	-	-	0.110	-
E3	-	9.20	-	-	0.362	-
e	2.54 TYP			0.1 BSC		
F	-	3.00	-	-	0.118	-
F1	-	1.36	-	-	0.054	-
F2	-	1.10	-	-	0.043	-
F3	-	13.08	-	-	0.515	-
F4	10.03	10.08	10.13	0.395	0.397	0.399
ϕ	2.58	3.60	3.62	0.102	0.142	0.143
H	45°			45°		

RESTRICTIONS ON PRODUCT USE

- The information contained herein is subject to change without notice.
- BYD Microelectronics Co., Ltd. (short for BME) exerts the greatest possible effort to ensure high quality and reliability. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing BME products, to comply with the standards of safety in making a safe design for the entire system, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue. In developing your designs, please ensure that BME products are used within specified operating ranges as set forth in the most recent BME products specifications.
- The BME products listed in this document are intended for usage in general electronics applications (personal equipment, office equipment, domestic appliances, etc.). These BME products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury (“Unintended Usage”). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of BME products listed in this document shall be made at the customer’s own risk.
- BME is not responsible for any problems caused by circuits or diagrams described herein whose related industrial properties, patents, or other rights belong to third parties. The application circuit examples explain typical applications of the products, and do not guarantee the success of any specific mass-production design.